

a number of bumps formed respectively in said through-holes in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

22. (Twice Amended) A semiconductor device comprising:

a wiring substrate having a predetermined pattern of wiring formed on one surface;

a semiconductor chip disposed on the other surface of said wiring substrate and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein said chip electrodes are arranged parallel to an edge of said semiconductor chip and said wiring is bent at at least one position;

said wiring substrate having a number of through-holes;

a number of bumps formed respectively in said through-holes in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

23. (Twice Amended) A semiconductor device comprising:

a wiring substrate having a predetermined pattern of wiring formed on one surface;

a semiconductor chip disposed on the other surface of said wiring substrate and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein said chip electrodes are arranged parallel to an edge of said semiconductor chip and said wiring has an end width larger than an inter-electrode distance between said chip electrodes;

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E1  
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f1

said wiring substrate having a number of through-holes;  
a number of bumps formed respectively in said through-holes in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and  
a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

Subf2  
E2

27. (Twice Amended) A semiconductor device comprising:  
a wiring substrate having a predetermined pattern of wiring formed on one surface;  
a semiconductor chip disposed on said one surface of said wiring substrate and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein said chip electrodes are arranged from an edge of said semiconductor chip toward its inner side;  
a number of bumps disposed on said wiring respectively in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and  
a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

28. (Twice Amended) A semiconductor device comprising:  
a wiring substrate having a predetermined pattern of wiring formed on one surface;  
a semiconductor chip disposed on said one surface of said wiring substrate and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein said chip electrodes are arranged parallel to an edge of said semiconductor chip and said wiring is bent at at least one position;

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*Cont E2*  
*Sub f2*  
a number of bumps disposed on said wiring respectively in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

29. (Twice Amended) A semiconductor device comprising:

a wiring substrate having a predetermined pattern of wiring formed on one surface;

a semiconductor chip disposed on said one surface of said wiring substrate and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein said chip electrodes are arranged parallel to an edge of said semiconductor chip and said wiring has an end width larger than an inter-electrode distance between said chip electrodes;

a number of bumps disposed on said wiring respectively in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

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33. (Twice Amended) A semiconductor device comprising:

a TAB (tape automated bonding) tape having a predetermined pattern of wiring formed on one surface;

a semiconductor chip disposed on the other surface of said TAB tape and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein said chip electrodes are arranged from an edge of said semiconductor chip toward its inner side;

said TAB tape having a number of through-holes;

und  
E3

a number of bumps formed respectively in said through-holes in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

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f01

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

34. (Twice Amended) A semiconductor device comprising:

a TAB (tape automated bonding) tape having a predetermined pattern of wiring formed on one surface;

a semiconductor chip disposed on the other surface of said TAB tape and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein said chip electrodes are arranged parallel to an edge of said semiconductor chip and said wiring is bent at at least one position;

said TAB tape having a number of through-holes;

a number of bumps formed respectively in said through-holes in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

35. (Twice Amended) A semiconductor device comprising:

a TAB (tape automated bonding) tape having a predetermined pattern of wiring formed on one surface;

a semiconductor chip disposed on the other surface of said TAB tape and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein

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E3  
Sub f3  
said chip electrodes are arranged parallel to an edge of said semiconductor chip and said wiring has an end width larger than an inter-electrode distance between said chip electrodes;

said TAB tape having a number of through-holes;

a number of bumps formed respectively in said through-holes in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

E4  
Sub f4  
39. (Twice Amended) A semiconductor device comprising:

a TAB tape having a predetermined pattern of wiring formed on one surface;

a semiconductor chip disposed on said one surface of said TAB tape and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein said chip electrodes are arranged from an edge of said semiconductor chip toward its inner side;

a number of bumps disposed on said wiring respectively in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

40. (Twice Amended) A semiconductor device comprising:

a TAB tape having a predetermined pattern of wiring formed on one surface;

a semiconductor chip disposed on said one surface of said TAB tape and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein

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said chip electrodes are arranged parallel to an edge of said semiconductor chip and said wiring is bent at at least one position;

a number of bumps disposed on said wiring respectively in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

41. (Twice Amended) A semiconductor device comprising:

a TAB tape having a predetermined pattern of wiring formed on one surface;

a semiconductor chip disposed on said one surface of said TAB tape and having at least one chip electrode set comprising at least two chip electrodes in a common wiring layer, wherein said chip electrodes are arranged parallel to an edge of said semiconductor chip and said wiring has an end width larger than an inter-electrode distance between said chip electrodes;

a number of bumps disposed on said wiring respectively in conforming relationship with said at least two chip electrodes and electrically connecting said wiring with said at least two chip electrodes; and

a single external bump pad electrically connected through said common wiring layer to said at least two chip electrodes.

#### REMARKS

Independent claims 21-23, 27-29, 33-35 and 39-41 have been amended to clarify that the claimed invention has a single external bump pad electrically connected to the at least two chip electrodes. No new matter has been entered. Pursuant to 37 CFR § 1.121, a marked copy of the amended claims showing changes made therein accompanies this Amendment.

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